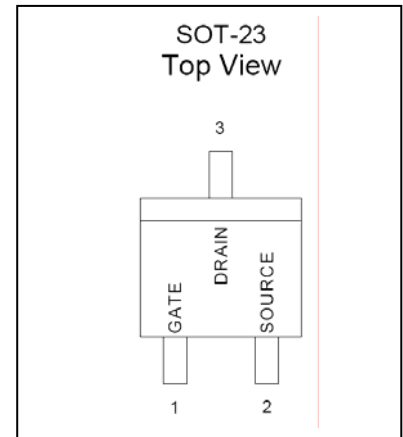
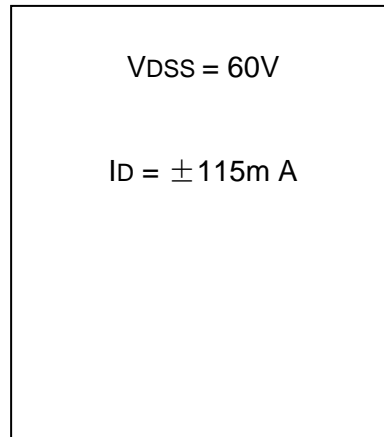
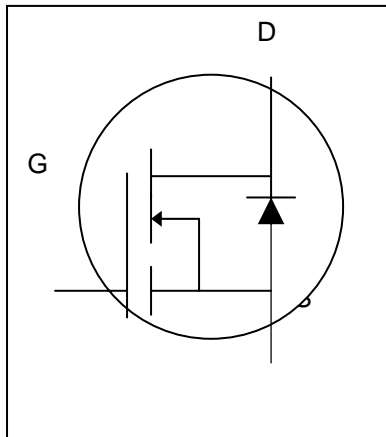


- Advanced Process Technology
- Ultra low On-Resistance Provides Higher Efficiency
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and V_{DS} (on) Specified at Elevated Temperature

DESCRIPTION



ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage($R_{GS}=1.0M\Omega$)	V_{DGR}	60	V
Drain to Current – Continuous	I_D	± 115	mA
– Pulsed	I_{DM}	± 800	mA
Gate-to-Source Voltage – Continue	V_{GS}	± 20	V
– Non-repetitive	V_{GSM}	± 40	V
Total Power Dissipation	P_D	225	mW
Derate above 25 °C		1.8	mW/°C
Single Pulse Drain-to-Source Avalanche Energy – $T_J = 25\text{ °C}$ ($V_{DD} = 50V$, $V_{GS} = 10V$, $I_{AS} = 0.8A$, $L = 30mH$, $R_G = 25\Omega$)	E_{AS}	9.6	mJ
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C
Thermal Resistance – Junction to Ambient	θ_{JA}	417	°C/W
Maximum Lead Temperature for Soldering Purpose, 1/8" from case for 10 seconds	T_L	300	°C

ELECTRICAL CHARACTERISTICS

Unless otherwise specified, $T_J = 25^\circ\text{C}$.

Characteristic		B02N7002			Units
		Min	Typ	Max	
Drain-Source Breakdown Voltage ($V_{GS} = 0\text{ V}$, $I_D = 10\text{ }\mu\text{A}$)	$V_{(BR)DSS}$	60			V
Drain-Source Leakage Current ($V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$) ($V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125^\circ\text{C}$)	I_{DSS}			1.0 0.5	μA mA
Gate-Source Leakage Current-Forward ($V_{gsf} = 20\text{ V}$)	I_{GSSF}			100	nA
Gate-Source Leakage Current-Reverse ($V_{gsf} = -20\text{ V}$)	I_{GSSF}			-100	nA
Gate Threshold Voltage * ($V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$)	$V_{GS(th)}$	1.0		2.5	V
On-State Drain Current ($V_{DS} \geq 2.0 V_{DS(on)}$, $V_{GS} = 10\text{ V}$)	$I_{D(on)}$	500			mA
Static Drain-Source On-Resistance * ($V_{GS} = 10\text{ V}$, $I_D = 0.5\text{ A}$) ($V_{GS} = 10\text{ V}$, $I_D = 0.5\text{ A}$, $T_c = 125^\circ\text{C}$) ($V_{GS} = 5.0\text{ V}$, $I_D = 50\text{ mA}$) ($V_{GS} = 5.0\text{ V}$, $I_D = 50\text{ mA}$, $T_c = 125^\circ\text{C}$)	$R_{DS(on)}$			7.5 13.5 7.5 13.5	Ω
Drain-Source On-Voltage * ($V_{GS} = 10\text{ V}$, $I_D = 0.5\text{ A}$) ($V_{GS} = 5.0\text{ V}$, $I_D = 50\text{ mA}$)	$V_{DS(on)}$			3.75 0.375	V
Forward Transconductance ($V_{DS} \geq 2.0 V_{DS(on)}$, $I_D = 200\text{ mA}$) *	g_{FS}	80			mmhos
Input Capacitance	$(V_{DS} = 25\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{ MHz}$)	C_{iss}		50	pF
Output Capacitance		C_{oss}		25	pF
Reverse Transfer Capacitance		C_{rss}		5.0	pF
Turn-On Delay Time	$(V_{DD} = 25\text{ V}$, $I_D = 500\text{ mA}$, $V_{gen} = 10\text{ V}$, $R_G = 25\Omega$, $R_L = 50\Omega$) *	$t_{d(on)}$		20	ns
Turn-Off Delay Time		$t_{d(off)}$		40	ns
Diode Forward On-Voltage ($I_S = 115\text{ mA}$, $V_{GS} = 0\text{ V}$)	V_{SD}			-1.5	V
Source Current Continuous (Body Diode)	I_S			-115	mA
Source Current Pulsed	I_{SM}			-800	mA

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

TYPICAL ELECTRICAL CHARACTERISTICS

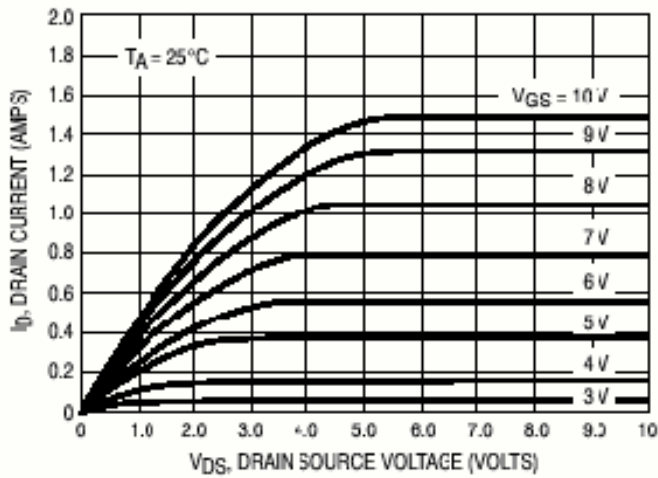


Figure 1. Ohmic Region

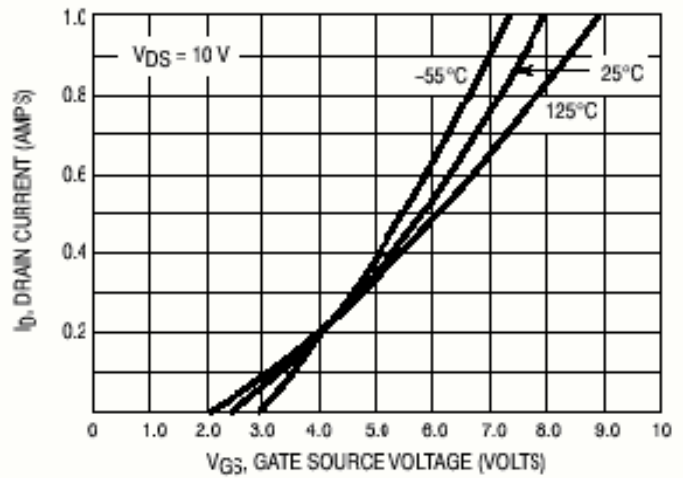


Figure 2. Transfer Characteristics

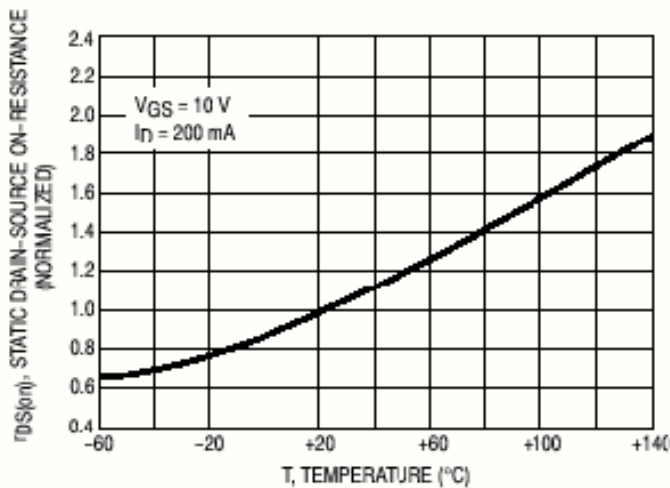


Figure 3. Temperature versus Static Drain-Source On-Resistance

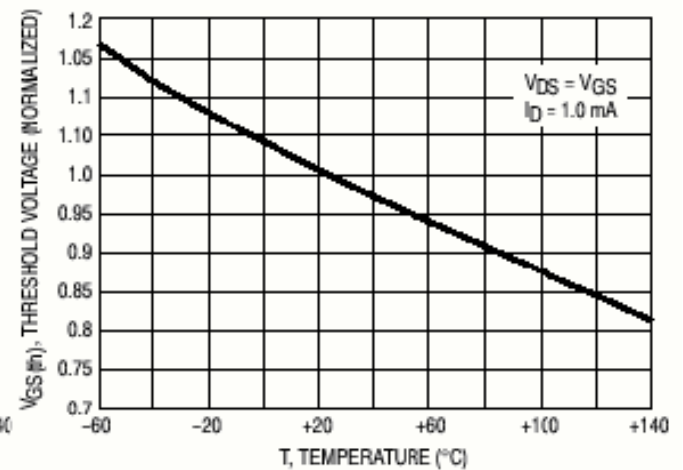


Figure 4. Temperature versus Gate Threshold Voltage

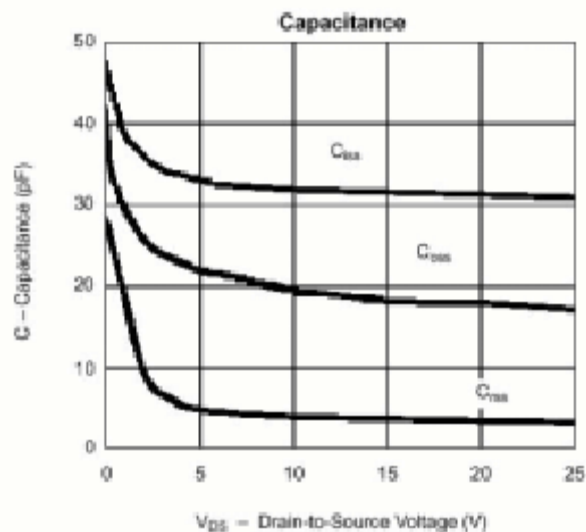
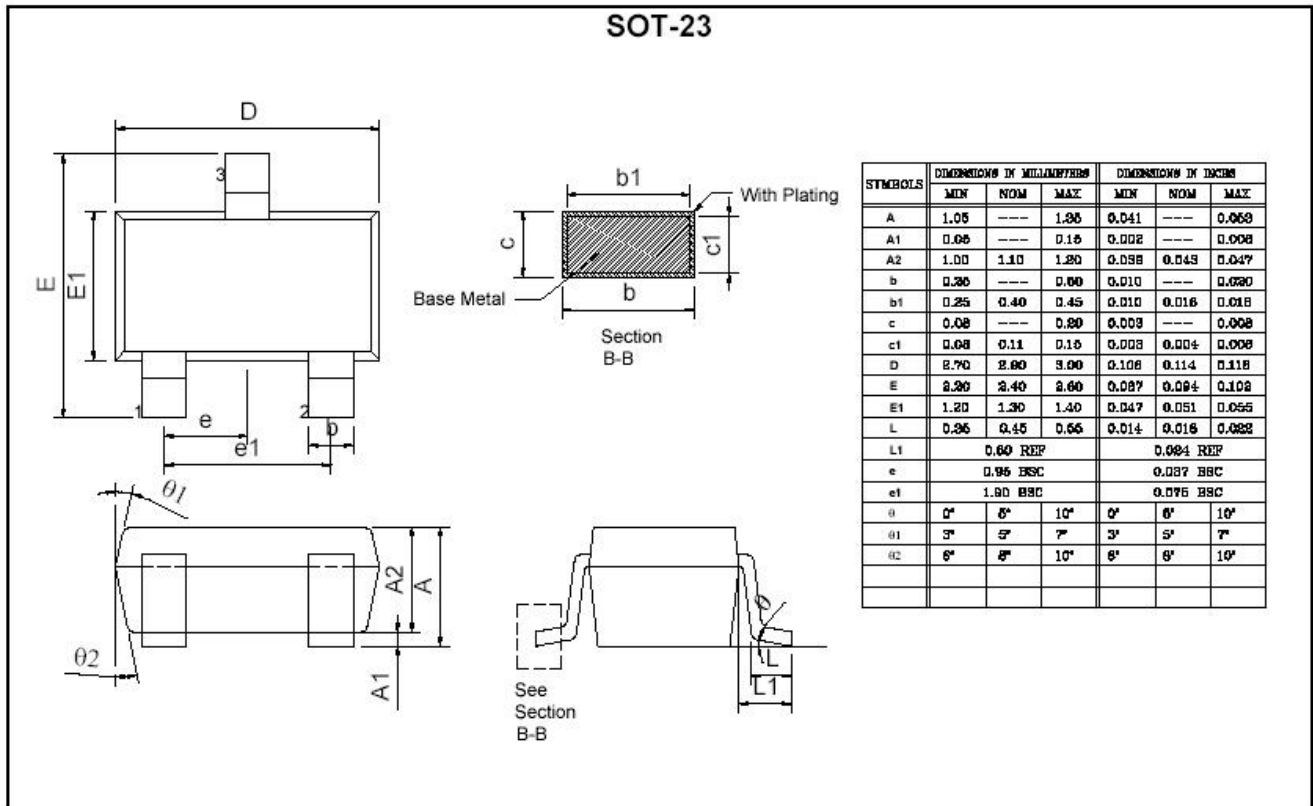


Figure 5: Capacitance

PACKAGE DIMENSION



IMPORTANT NOTICE

Blue Electronic reserves the right to mark change to its products or discontinue any product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

A few applications using product may involve potential risk of death, personal injury, or severe property or environmental damage. Blue Electronic product are not designed, intended, authorized or warranted to be suitable for use in life-support applications devices or systems or other critical applications. Use of Blue Electronic products in such application is understood to be fully at the risk of the customer. In order to minimize risks associated with the customer's applications, the customer should provide adequate design and operating safeguards